PMV20XNEA
20 V, N-channel Trench MOSFET
9 March 2016
Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection $>2 \mathrm{kV}$ HBM
- AEC-Q101 qualified


## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits


## 4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{V}_{\mathrm{DS}}$ | drain-source voltage | $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ |  | - | - | 20 | V |
| $\mathrm{~V}_{G S}$ | gate-source voltage |  |  | -12 | - | 12 | V |
| $\mathrm{I}_{\mathrm{D}}$ | drain current | $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V} ; \mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$ | $[1]$ | - | - | 6.3 | A |
| Static characteristics | drain-source on-state <br> resistance | $\mathrm{V}_{G S}=4.5 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=6.3 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ |  | - | 16 | 20 | $\mathrm{~m} \Omega$ |
| $\mathrm{R}_{\mathrm{DSon}}$ |  |  |  |  |  |  |  |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain $6 \mathrm{~cm}^{2}$.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| :--- | :--- | :--- | :--- | :--- |
| 1 | G | gate |  |  |
| 2 | S | source |  |  |
| 3 | D | drain |  |  |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |  |  |
| :--- | :--- | :--- | :--- |
|  | Name | Description | Version |
| PMV20XNEA | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code <br> $[1]$ |
| :--- | :--- |
| PMV20XNEA | DT\% |

[1] \% = placeholder for manufacturing site code

## 8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {DS }}$ | drain-source voltage | $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ |  | - | 20 | V |
| $\mathrm{V}_{\mathrm{GS}}$ | gate-source voltage |  |  | -12 | 12 | V |
| $\mathrm{I}_{\mathrm{D}}$ | drain current | $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V} ; \mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$ | [1] | - | 6.3 | A |
|  |  | $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V} ; \mathrm{T}_{\text {amb }}=100^{\circ} \mathrm{C}$ | [1] | - | 4 | A |
| $\mathrm{I}_{\mathrm{DM}}$ | peak drain current | $\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$; single pulse; $\mathrm{t}_{\mathrm{p}} \leq 10 \mu \mathrm{~s}$ |  | - | 25 | A |
| $\mathrm{E}_{\mathrm{DS}(\mathrm{AL}) \mathrm{S}}$ | non-repetitive drain-source avalanche energy | $T_{j \text { (nit) }}=25^{\circ} \mathrm{C} ; \mathrm{I}_{\mathrm{D}}=1.6 \mathrm{~A}$; DUT in avalanche (unclamped) |  | - | 16 | mJ |
| $\mathrm{P}_{\text {tot }}$ | total power dissipation | $\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$ | [2] | - | 0.46 | W |
|  |  |  | [1] | - | 1.19 | W |
|  |  | $\mathrm{T}_{\text {sp }}=25^{\circ} \mathrm{C}$ |  | - | 6.94 | W |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  |  | -55 | 150 | ${ }^{\circ} \mathrm{C}$ |
| Tamb | ambient temperature |  |  | -55 | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | storage temperature |  |  | -65 | 150 | ${ }^{\circ} \mathrm{C}$ |
| Source-drain diode |  |  |  |  |  |  |
| $\mathrm{I}_{\text {S }}$ | source current | $\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$ | [1] | - | 0.73 | A |
| ESD maximum rating |  |  |  |  |  |  |
| $V_{\text {ESD }}$ | electrostatic discharge voltage | HBM | [3] | - | 2000 | V |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain $6 \mathrm{~cm}^{2}$.
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
[3] Measured between all pins.


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$
P_{d e r}=\frac{P_{\text {tot }}}{P_{\text {tot }\left(25^{\circ} \mathrm{C}\right)}} \times 100 \%
$$



Fig. 2. Normalized continuous drain current as a function of junction temperature

$$
I_{d e r}=\frac{I_{D}}{I_{D\left(25^{\circ} \mathrm{C}\right)}} \times 100 \%
$$



Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\text {th(j-a) }}$ | thermal resistance from junction to ambient | in free air | [1] | - | 227 | 270 | K/W |
|  |  |  | [2] | - | 91 | 105 | K/W |
| $\mathrm{R}_{\mathrm{th}(\mathrm{j}-\mathrm{sp})}$ | thermal resistance from junction to solder point |  |  | - | 13 | 18 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain $6 \mathrm{~cm}^{2}$.


FR4 PCB, standard footprint
Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values


FR4 PCB, mounting pad for drain $6 \mathrm{~cm}^{2}$
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values PMV20XNEA

## 10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Static characteristics |  |  |  |  |  |  |
| $\mathrm{V}_{\text {(BR) }{ }^{\text {dss }}}$ | drain-source breakdown voltage | $\mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A} ; \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | 20 | - | - | V |
| $V_{\text {GSth }}$ | gate-source threshold voltage | $\mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A} ; \mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{G S} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | 0.75 | 1 | 1.25 | V |
| IDSs | drain leakage current | $V_{D S}=20 \mathrm{~V} ; \mathrm{V}_{G S}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | - | 1 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\text {GSS }}$ | gate leakage current | $\mathrm{V}_{G S}=12 \mathrm{~V} ; \mathrm{V}_{\mathrm{DS}}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | - | 10 | $\mu \mathrm{A}$ |
|  |  | $V_{G S}=-12 \mathrm{~V} ; \mathrm{V}_{\text {DS }}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | - | -10 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{G S}=4.5 \mathrm{~V} ; \mathrm{V}_{\text {DS }}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | - | 5 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{G S}=-4.5 \mathrm{~V} ; \mathrm{V}_{\mathrm{DS}}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | - | -5 | $\mu \mathrm{A}$ |
| $\mathrm{R}_{\text {DSon }}$ | drain-source on-state resistance | $V_{G S}=4.5 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=6.3 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | 16 | 20 | $\mathrm{m} \Omega$ |
|  |  | $V_{G S}=4.5 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=6.3 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=150{ }^{\circ} \mathrm{C}$ | - | 24 | 30 | $\mathrm{m} \Omega$ |
|  |  | $V_{G S}=2.5 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=4.8 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | 24 | 34 | $\mathrm{m} \Omega$ |
| gfs | forward transconductance | $V_{D S}=10 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=6.3 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | 26.8 | - | S |
| $\mathrm{R}_{\mathrm{G}}$ | gate resistance | $\mathrm{f}=1 \mathrm{MHz}$ | - | 7.2 | - | $\Omega$ |
| Dynamic characteristics |  |  |  |  |  |  |
| $\mathrm{Q}_{\mathrm{G} \text { (tot) }}$ | total gate charge | $\begin{aligned} & \mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=6.3 \mathrm{~A} ; \mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V} ; \\ & \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 9.9 | 15 | nC |
| $\mathrm{Q}_{\mathrm{GS}}$ | gate-source charge |  | - | 1.4 | - | nC |
| $Q_{G D}$ | gate-drain charge |  | - | 3.1 | - | nC |
| $\mathrm{C}_{\text {iss }}$ | input capacitance | $\begin{aligned} & \mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V} ; \mathrm{f}=1 \mathrm{MHz} ; \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V} ; \\ & \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 930 | - | pF |
| $\mathrm{C}_{\text {oss }}$ | output capacitance |  | - | 178 | - | pF |
| $\mathrm{C}_{\text {rss }}$ | reverse transfer capacitance |  | - | 144 | - | pF |
| $\mathrm{t}_{\mathrm{d} \text { (on) }}$ | turn-on delay time | $\begin{aligned} & \mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=6.3 \mathrm{~A} ; \mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V} ; \\ & \mathrm{R}_{\mathrm{G}(\mathrm{ext})}=6 \Omega ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 16 | - | ns |
| $\mathrm{t}_{\mathrm{r}}$ | rise time |  | - | 40 | - | ns |
| $t_{\text {d(off) }}$ | turn-off delay time |  | - | 44 | - | ns |
| $\mathrm{t}_{\mathrm{f}}$ | fall time |  | - | 22 | - | ns |
| Source-drain diode |  |  |  |  |  |  |
| $V_{S D}$ | source-drain voltage | $\mathrm{I}_{\mathrm{S}}=0.9 \mathrm{~A} ; \mathrm{V}_{G S}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | - | 0.7 | 1.2 | V |



Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

$\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{DS}}=5 \mathrm{~V}$
Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$\mathrm{I}_{\mathrm{D}}=2.2 \mathrm{~A}$
Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$\mathrm{I}_{\mathrm{D}}=0.25 \mathrm{~mA} ; \mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{\mathrm{GS}}$
Fig. 12. Gate-source threshold voltage as a function of junction temperature


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$
a=\frac{R_{D S o n}}{R_{D S o n}\left(25^{\circ} \mathrm{C}\right)}
$$


$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}$
Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$\mathrm{I}_{\mathrm{D}}=6.32 \mathrm{~A} ; \mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V} ; \mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$
Fig. 14. Gate-source voltage as a function of gate charge; typical values


Fig. 15. MOSFET transistor: Gate charge waveform definitions

$V_{G S}=0 \mathrm{~V}$
Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information



Fig. 17. Duty cycle definition

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline

Plastic surface-mounted package; 3 leads SOT23

detail X


Dimensions (mm are the original dimensions)

sot023_po

| Outline version | References |  |  | European projection | Issue date |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | IEC | JEDEC | JEITA |  |  |
| SOT23 |  | TO-236AB |  | $\square$ (¢) | $\begin{aligned} & 14-06-19 \\ & 14-09-22 \end{aligned}$ |

Fig. 18. Package outline TO-236AB (SOT23)

## 13. Soldering



Q17DA solder lands
---. solder resist
solder paste
!-ーー! occupied area

Dimensions in mm
sot023_fr
Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

## 14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
| :--- | :--- | :--- | :--- | :--- |
| PMV20XNEA v.1 | 20160309 | Product data sheet | - | - |

## 15. Legal information

### 15.1 Data sheet status

| Document <br> status [1][2] | Product <br> status [3] | Definition |
| :--- | :--- | :--- |
| Objective <br> [short] data <br> sheet | Development | This document contains data from <br> the objective specification for product <br> development. |
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